



# BAV19W thru BAV21W

## Silicon Epitaxial Planar Diodes

### Features

- Fast switching speed
- Surface mount package ideally suited for automatic insertion

SOD-123



Marking : JX



1Cathode 2Anode

### Absolute Maximum Ratings (Ta=25°C)

Parameter	Symbol	Value	Unit
Repetitive Peak Reverse Voltage	$V_{RRM}$	120 200 250	V
Reverse Voltage	$V_R$	100 150 200	V
Average Rectified Forward Current	$I_{F(AV)}$	200	mA
Forward Continuous Current	$I_{FM}$	400	mA
Repetitive Peak Forward Current	$I_{FRM}$	625	mA
Non-repetitive Peak Forward Surge Current	$I_{FSM}$	2.5 0.5	A
Power Dissipation	$P_d$	250	mW
Operating and Storage Temperature Range	$T_J, T_{STG}$	- 65 to + 150	°C

### Characteristics (Ta=25°C)

Parameter	Symbol	Min.	Max.	Unit
Forward Voltage at $I_F = 100$ mA at $I_F = 200$ mA	$V_F$	- -	1 1.25	V
Reverse Breakdown Voltage at $I_R = 100$ $\mu$ A	$V_{(BR)R}$	120 200 250	- - -	V
Reverse Current at $V_R = 100$ V at $V_R = 150$ V at $V_R = 200$ V	$I_R$	- - -	100 100 100	nA
Total Capacitance at $V_R = 0$ , $f = 1$ MHz	$C_T$	-	5	pF
Reverse Recovery Time at $I_F = I_R = 30$ mA, $I_{rr} = 0.1I_R$ , $R_L = 100$ $\Omega$	$t_{rr}$	-	50	ns



## Rating And Characteristics Curves

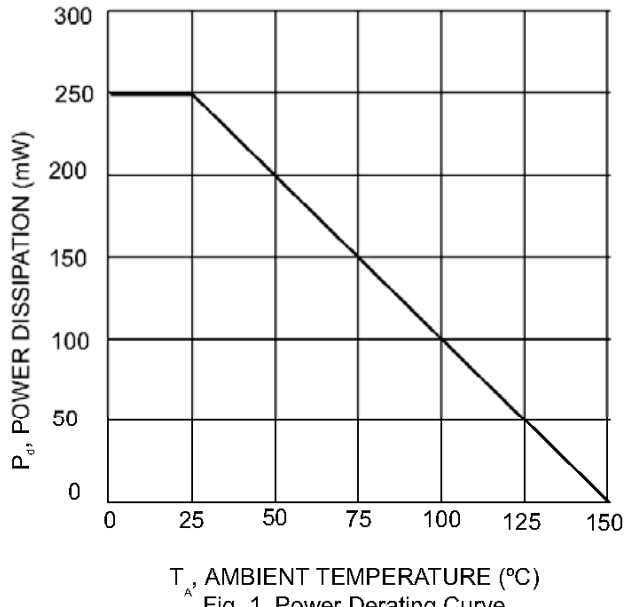


Fig. 1 Power Derating Curve

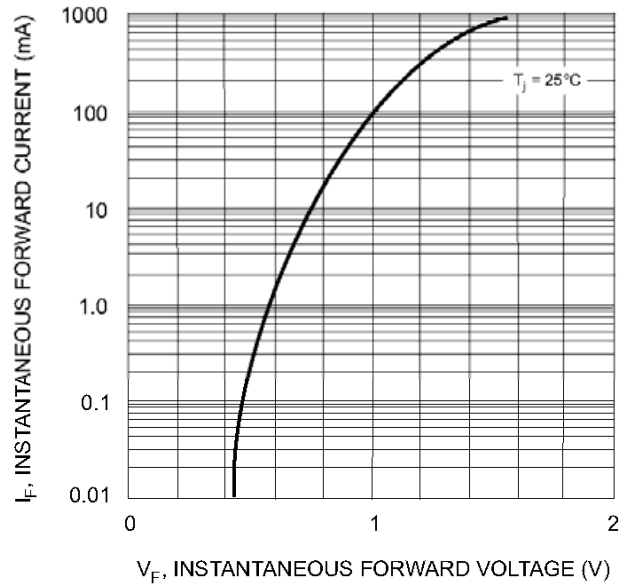


Fig. 2 Typical Forward Characteristics

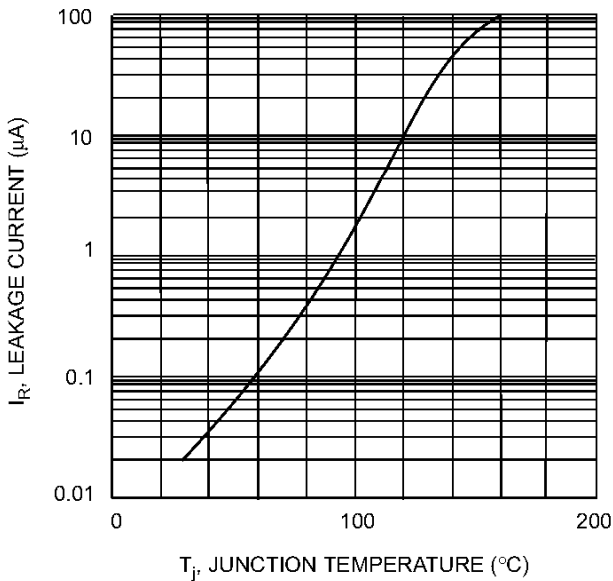


Fig. 3 Leakage Current vs Junction Temperature

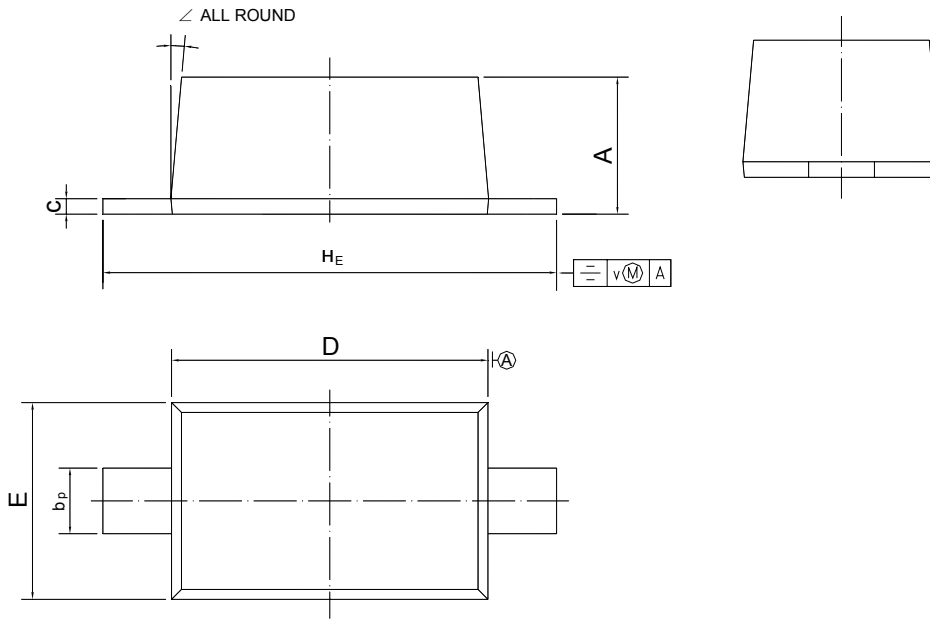


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### Package Outline

SOD-123



UNIT	A	b <sub>p</sub>	c	D	E	H <sub>E</sub>	v	∠
mm	1.15 1.05	0.6 0.5	0.135 0.100	2.7 2.6	1.65 1.55	3.85 3.55	0.2	5°

### Ordering Information

Device	Package	Shipping
BAV19W thru BAV21W	SOD-123	3000/Tape&Reel (7 inches)